

SANYO

No.1628C

2SC3644

NPN Triple Diffused Planar Silicon Transistor

Ultrahigh-Definition Display
Horizontal Deflection Output Applications

Features

- High reliability (Adoption of HVP process).
- High speed.
- High breakdown voltage.
- Adoption of MBIT process.

勝特力電材超市-龍山店 886-3-5773766
勝特力電材超市-光復店 886-3-5729570
勝特力電子(上海) 86-21-34970699
勝特力電子(深圳) 86-755-83298787
<http://www.100y.com.tw>

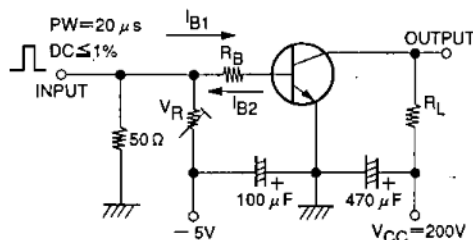
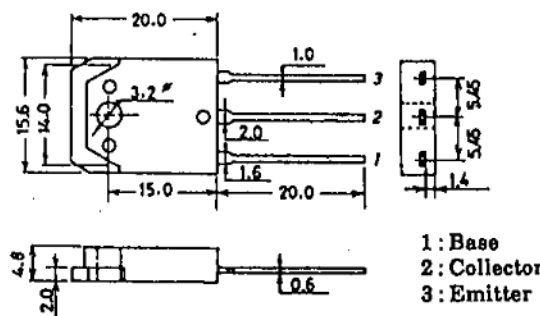
Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

			unit
Collector-to-Base Voltage	V_{CB0}	1200	V
Collector-to-Emitter Voltage	V_{CEO}	800	V
Emitter-to-Base Voltage	V_{EBO}	7	V
Collector Current	I_C	12	A
Collector Current (Pulse)	I_{CP}	25	A
Collector Dissipation	P_C	150	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

$T_c = 25^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

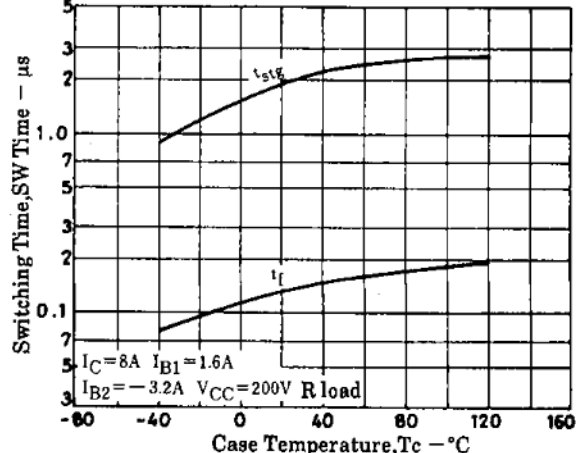
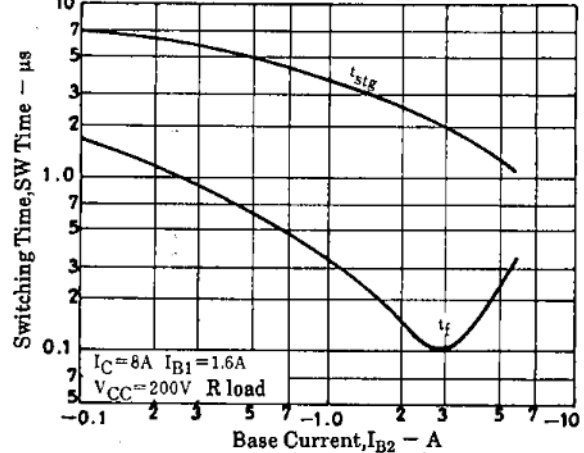
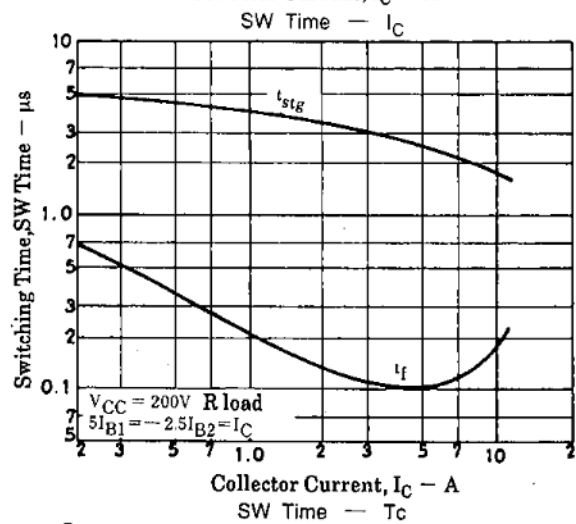
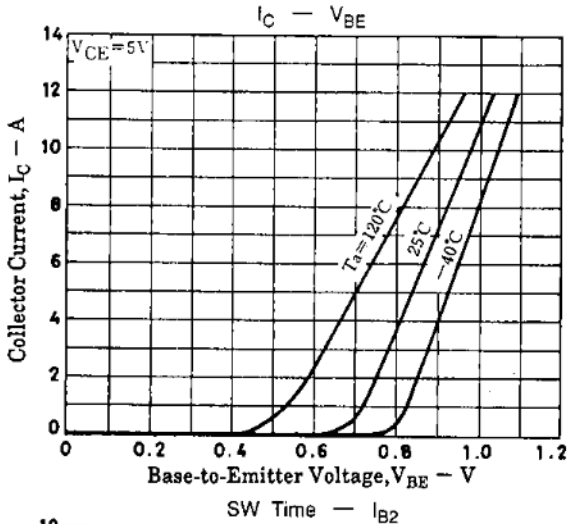
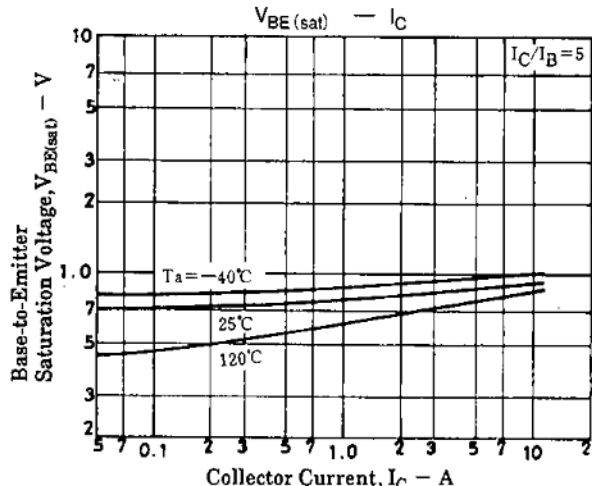
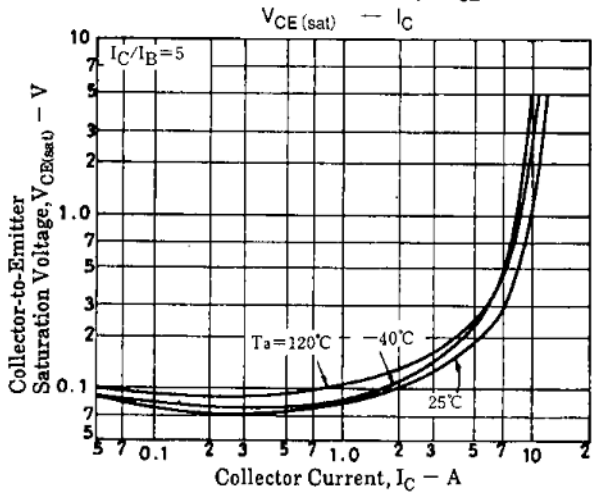
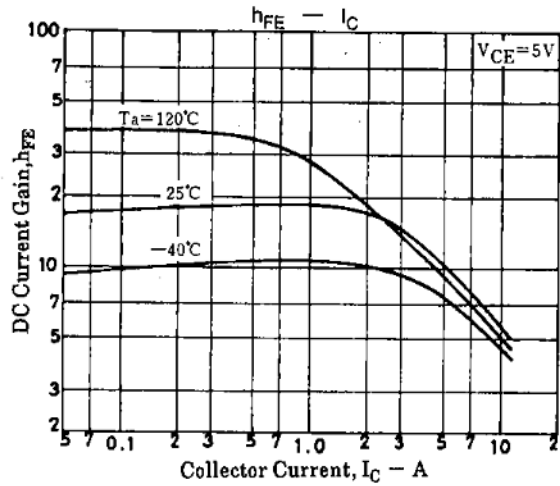
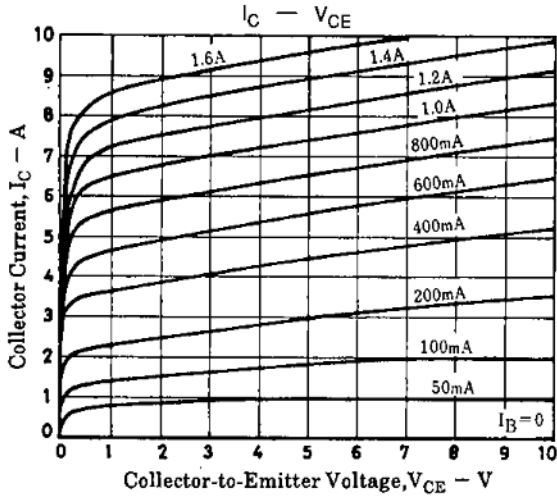
			min	typ	max	unit
Collector Cutoff Current	I_{CB0}	$V_{CB} = 800\text{V}, I_E = 0$			10	μA
	I_{CES}	$V_{CE} = 1200\text{V}, R_{BE} = 0$			0.5	mA
C-E Sustaining Voltage	$V_{CEO(sus)}$	$I_C = 100\text{mA}, I_B = 0$	800			V
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 5\text{V}, I_C = 0$			1	mA
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 8\text{A}, I_B = 1.6\text{A}$			5	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = 8\text{A}, I_B = 1.6\text{A}$			1.5	V
DC Current Gain	h_{FE}	$V_{CE} = 5\text{V}, I_C = 1.6\text{A}$	8			
Storage Time	t_{stg}	$I_C = 8\text{A}, I_{B1} = 1.6\text{A}, I_{B2} = -3.2\text{A}$			3.0	μs
Fall Time	t_f	$I_C = 8\text{A}, I_{B1} = 1.6\text{A}, I_{B2} = -3.2\text{A}$		0.1	0.2	μs

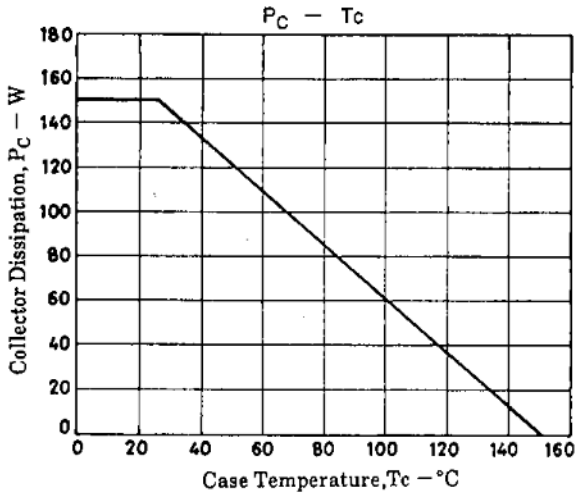
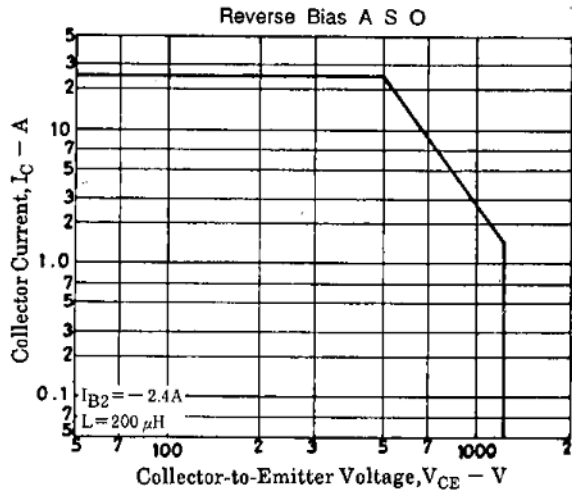
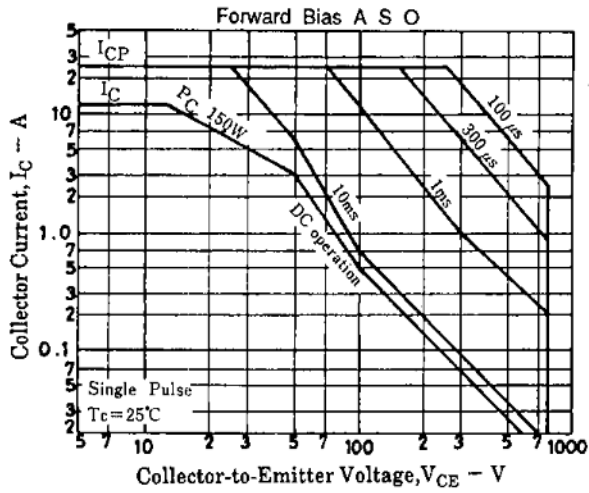
Switching Time Test Circuit**Package Dimensions 2022A**
(unit: mm)

SANYO: TO3PB

SANYO Electric Co., Ltd. Semiconductor Business Headquarters

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN





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